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CCS H 80



**NATIONAL STANDARD OF THE
PEOPLE'S REPUBLIC OF CHINA**

GB/T 24580-2009

**Test method for measuring Boron contamination in heavily
doped n-type silicon substrates by secondary ion mass
spectrometry**

重掺n型硅衬底中硼沾污的二次离子质谱检测方法

(English Translation)

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What this standard covers

This standard specifies the method of secondary ion mass spectrometry heavily doped n-type silicon substrate boron contamination. This standard applies to secondary ion mass spectrometry (SIMS) for heavily doped n-type single crystal silicon substrate material shed trace contamination (total) test. This standard applies to antimony, arsenic, doped with phosphorus concentration GB/T 24580-2009 | Test method for measuring Boron contamination in heavily doped n-type silicon substrates by secondary ion mass spectrometry

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Standards quoted by this document

ASTM E122